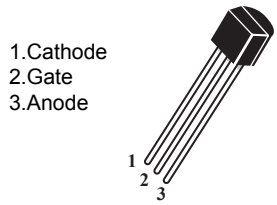
WEITRON

MCR100-6/MCR100-8

Sensitive Gate Silicon Controlled Rectifiers
Reverse Blocking Thyristors

Pb Lead(Pb)-Free

SCRs
0.8 A RMS
400/600 Voltage



TO-92

Maximum Ratings (T_A=25°C unless otherwise noted)

Rating	Symbol	MCR100-6	MCR100-8	Unit
Repetitive Peak Off-stage Voltage	V_{DRM}	400	600	V
Collector-Base Voltage	I_{TRMS}	0.8		A
Junction Temperature Range	T_J	+150		°C
Storage Temperature Range	T_{stg}	-55 to +150		°C

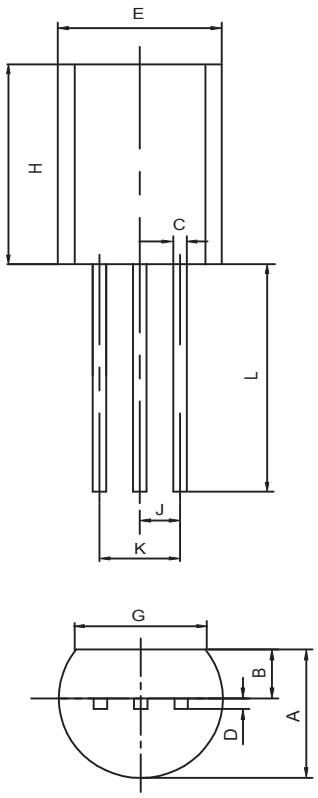
ELECTRICAL CHARACTERISTICS

Characteristics		Symbol		Min	Max	Unit
On State Voltage(1) I_{TM} = 1A		V_{TM}		-	1.7	V
Gate Trigger Voltage V_{AK} = 7V		V_{GT}		-	0.8	V
Peak Repetitve Forward and Reverse Blocking Voltage I_{DRM} = 10μA , V_{MAX} = 10V	MCR100-6 MCR100-8	V_{DRM}, V_{RRM}		400 600	-	V
Peak Forward or Reverse Blocking Current V_{AK} = Rated, V_{DRM} or V_{RRM}		I_{DRM}, I_{RRM}		-	10	μA
Holding Current I_{HL} = 20mA, A_V = 7V		I_H		-	5	mA
Gate Trigger Current V_{AK} = 7V		I_{GT}	A2 A1 A B	5 15 30 80	15 30 80 200	μA

Note 1. Forward current applied for 1 ms maximum duration, duty cycle ≤ 1%

TO-92 Outline Dimensions

unit:mm



TO-92		
Dim	**Min**	**Max**
A	3.30	3.70
B	1.10	1.40
C	0.38	0.55
D	0.36	0.51
E	4.40	4.70
G	3.43	-
H	4.30	4.70
J	1.270TYP	
K	2.44	2.64
L	14.10	14.50